



A Standard Interface for NAND Flash

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Agenda

NAND Flash Product Integration

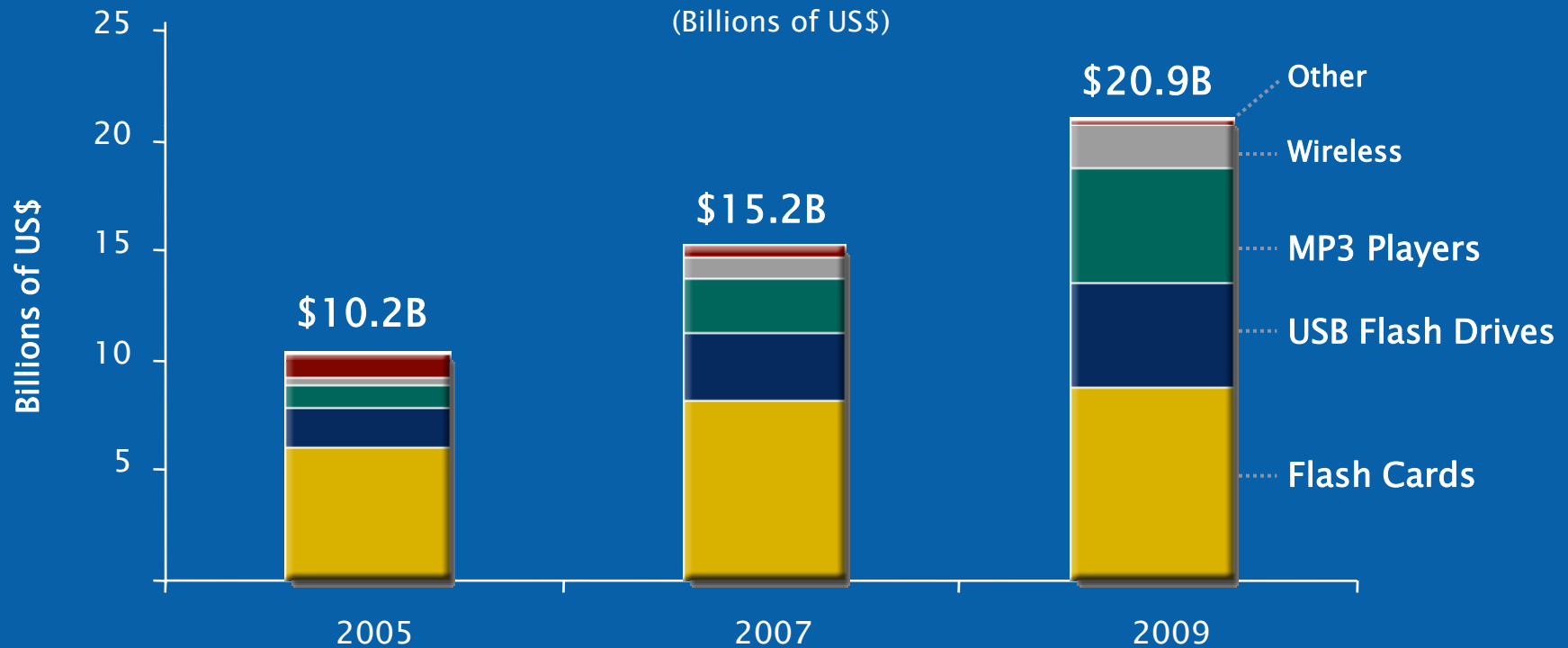
System problems with NAND Today

Open NAND Flash Interface (ONFI)
initiative overview

ONFI Technical Preview

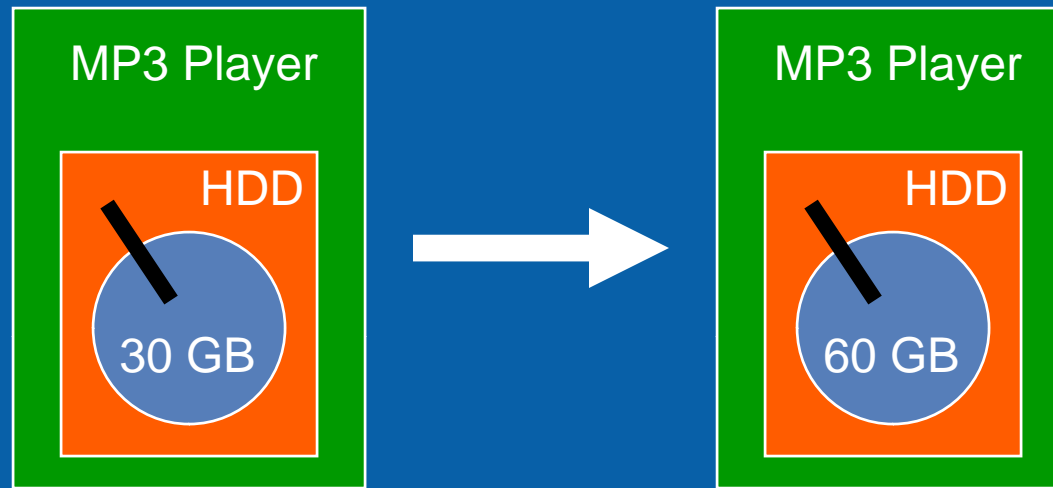
NAND Flash Is Becoming a Commodity Memory Product

Total NAND Market Segment
(Billions of US\$)



Source: WSTS, Micron Market Research

Product Update Cycle for HDD

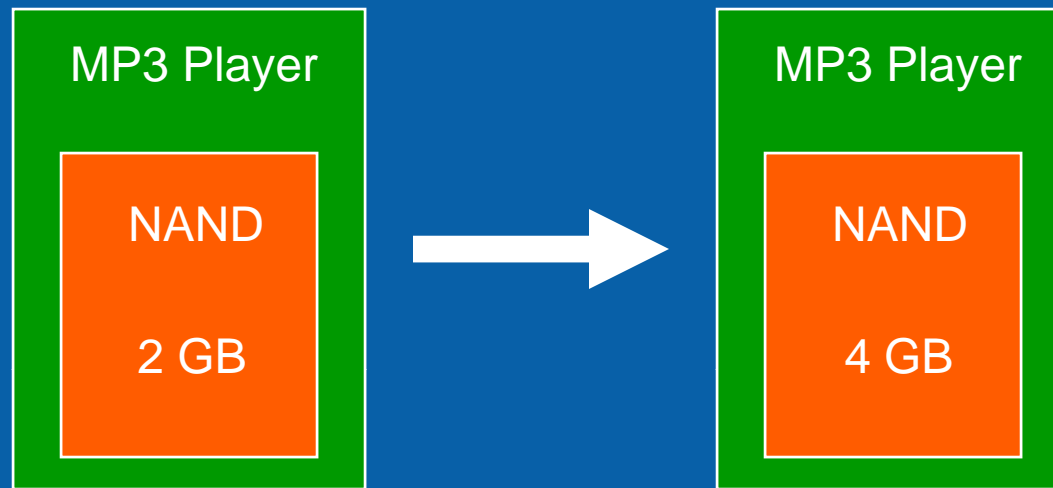


No software changes required

Product-level testing and validation focus

Physical and logical interface standard

Product Update Cycle for NAND



Firmware/software changes required

- Change device ID table to support new component
- Add support for new commands to maintain or increase performance

Complete re-test of firmware and/or software

Customer Challenges

Current NAND Flash device identification provides few, if any, details regarding the device's capabilities

What is needed to update a product to support new NAND Flash devices (from same or other vendor)?

- Architecture
 - Addressing into the NAND Flash memory array
 - ECC requirements
- Command set
 - Basic commands
 - Cache program
 - Cache read
 - Parallel operations
 - Status commands and status register bit definitions
- I/O timing

Why are there differences?

A Push for Higher Performance

Support parallel operations

- Array architecture
- Addressing
- Command set and status methods

Faster I/O timing

Faster array operations

Increase page size

A Push for Higher Density

Multi-Level Cell (MLC) technology

- Store 2 bits per memory cell instead of 1
- Result
 - Addressing change
 - Decreased performance
 - Reduced cell endurance
 - Stronger ECC requirements – 4 or more bits per 512 bytes
 - Lower cost per bit



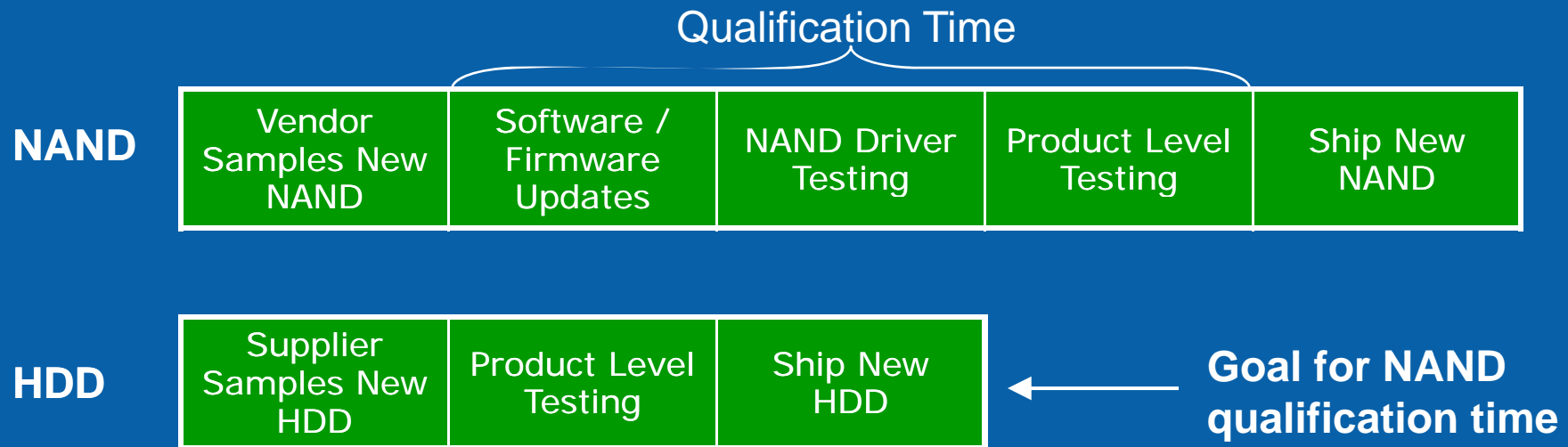
Long Product Update Cycles

Vendors developing features to support higher performance and density at the same time in isolation naturally leads to product inconsistency causing headaches for customers...

- Commands for new features are inconsistent
- I/O timing (clock cycle, setup, hold times) is inconsistent
- Addressing schemes are inconsistent

Unlike other commodity storage memories, NAND Flash does not have an industry-wide specification that provides product consistency in basic device behaviors

Delayed Opportunities...



NAND Flash requires more qualification time than other commodity memory products

Lost revenue opportunity that could be rectified with standard interface

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Intel's NAND Dilemma...

NAND Flash is an increasingly important Intel platform ingredient

- Robson technology highlights increasing role of NAND Flash in Intel's platform plans
- Intel's platforms have longevity and address numerous market segments, which requires support for a range of NAND Flash components
- Intel's stable platform must have the means for conveniently supporting the latest Flash components without having to be revamped

Current similar NAND Flash components do not allow for range of NAND to be accommodated in a platform

Similar: Basic Commands

Basic commands *typically* common

–Reset, Read ID, Read, Page Program, Erase, ...

More complex operations all over the map

Table 1. Command Sets

Function	1st. Cycle	2nd. Cycle
Read	00h	30h
Read for Copy Back	00h	35h
Read ID	90h	-
Reset	FFh	-
Page Program	80h	10h
Cache Program	80h	15h
Copy-Back Program	85h	10h
Block Erase	60h	D0h
Random Data Input ¹	85h	-
Random Data Output ¹	05h	E0h
Read Status	70h	

*Samsung K9K4G08U0M datasheet

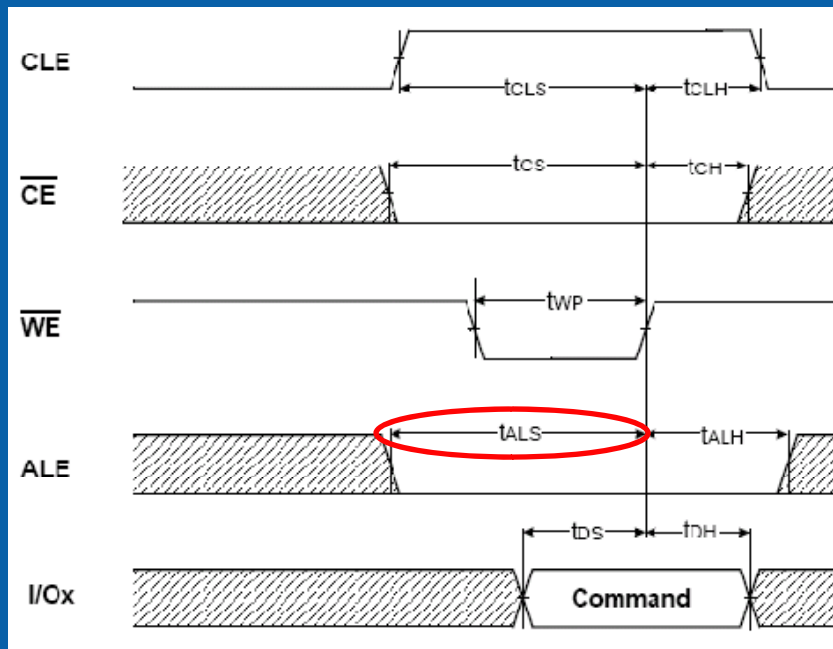
FUNCTION	1st CYCLE	2nd CYCLE
READ 1	00h	30h
READ FOR COPY-BACK	00h	35h
READ ID	90h	-
RESET	FFh	-
PAGE PROGRAM (start)	80h	10h
COPY BACK PGM (start)	85h	10h
CACHE PROGRAM	80h	15h
BLOCK ERASE	60h	D0h
READ STATUS REGISTER	70h	-
RANDOM DATA INPUT	85h	-
RANDOM DATA OUTPUT	05h	E0h
CACHE READ START	00h	31h
CACHE READ EXIT	34h	-
LOCK BLOCK	2Ah	-
LOCK TIGHT	2Ch	-
UNLOCK (start area)	23h	-
UNLOCK (end area)	24h	-
READ LOCK STATUS	7Ah	-

Table 4: Command Set

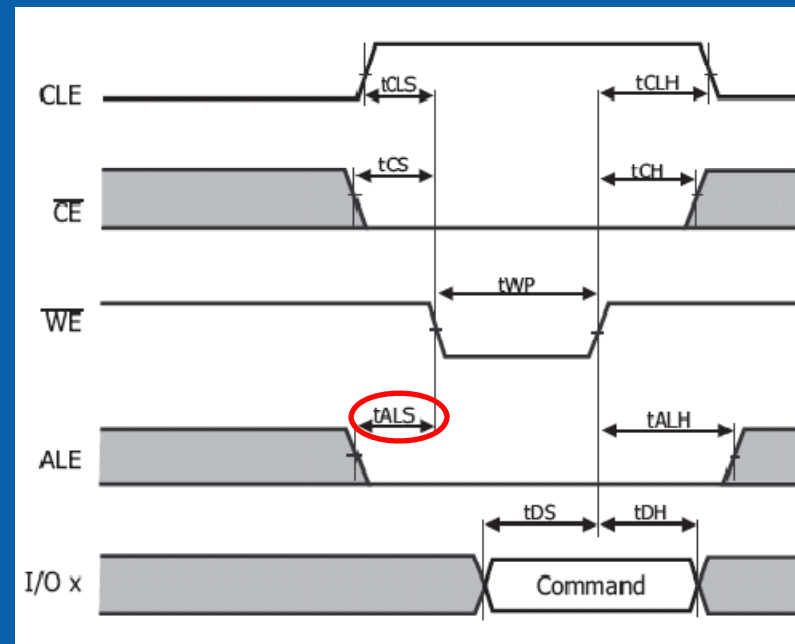
*Hynix HY27UG084G2M datasheet

Similar: Timing

Timing requirements are specified differently
Min/max values are not necessarily the same
for similar cycle time parts



*Samsung K9K4G08U0M datasheet



*Hynix HY27UG084G2M datasheet

Similar: Status Values

Status values dependent on command
 Often the same, but not required to be
 –Can you tell that these are the same??

I/O No.	Page Program	Block Erase	Cache Program	Read	Definition	
I/O 0	Pass/Fail	Pass/Fail	Pass/Fail(N)	Not use	Pass : "0"	Fail : "1"
I/O 1	Not use	Not use	Pass/Fail(N-1)	Not use	Pass : "0"	Fail : "1"
I/O 2	Not use	Not use	Not use	Not use	Don't -cared	
I/O 3	Not Use	Not Use	Not Use	Not Use	Don't -cared	
I/O 4	Not Use	Not Use	Not Use	Not Use	Don't -cared	
I/O 5	Ready/Busy	Ready/Busy	True Ready/Busy	Ready/Busy	Busy : "0"	Ready : "1"
I/O 6	Ready/Busy	Ready/Busy				
I/O 7	Write Protect	Write Protect				

*Hynix HY27UG084G2M datasheet

*Samsung K9K4G08U0M datasheet

IO	Page Program	Block Erase	Cache Program	Read	Cache Read	CODING
0	Pass / Fail	Pass / Fail	Pass / Fail (N)	NA		Pass: '0' Fail: '1'
1	NA	NA	Pass / Fail (N-1)	NA		Pass: '0' Fail: '1' (Only for Cache Program, else Don't care)
2	NA	NA	NA	NA		-
3	NA	NA	NA	NA		-
4	NA	NA	NA	NA		-
5	Ready/Busy	Ready/Busy	P/E/R Controller Bit	Ready/Busy	P/E/R Controller Bit	Active: '0' Idle: '1'
6	Ready/Busy	Ready/Busy	Cache Register Free	Ready/Busy	Ready/Busy	Busy: '0' Ready: '1'
7	Write Protect	Write Protect	Write Protect	Write Protect		Protected: '0' Not Protected: '1'



Similar: Read ID

The first and second byte are consistently manufacturer and device ID

The number of remaining bytes and what they mean is up in the air

*Samsung K9K4G08U0M datasheet

	Description
1 st Byte	Maker Code
2 nd Byte	Device Code
3 rd Byte	Don't care
4 th Byte	Page Size, Block Size, Spare Size, Organization

*Toshiba TH58NVG1S3AFT05 datasheet

	Description	I/O8	I/O7	I/O6	I/O5	I/O4	I/O3	I/O2	I/O1	Hex Data
1 st Data	Maker Code	1	0	0	1	1	0	0	0	98H
2 nd Data	Device Code	1	1	0	1	1	0	1	0	DAH
3 rd Data	Chip Number, Cell Type, PGM Page, Write Cache	0 or 1	0	0	0	0	0	0	1	81H or 01H
4 th Data	Page Size, Block Size, Redundant Size, Organization	0 or 1	0	0	1	0	1	0	1	95H or 15H
5 th Data	Plane Number, Plane Size	0 or 1	1	0	0	0	1	0	0	44H or C4H

Similar Hinders NAND Adoption

To deal with differences, the host must maintain a chip ID table of known devices

- Table contains read/write timings, organization, status bit meanings, etc for each known NAND Flash part

Situation has two major effects:

- Precludes intro of new NAND devices into existing designs
- Makes qualification cycles longer as each NAND device added requires changes to be comprehended

Similar to the ancient disk drive interfaces that required a list of disk drive types in a BIOS table

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Open NAND Flash Interface

Goals of Initiative:

To develop a standardized NAND Flash interface that allows interoperability between NAND devices

Accelerate time to market of NAND-based products

Technical Philosophy

ONFI shall ensure no pre-association with NAND Flash at host design is required

- Flash must self-describe features, capabilities, timings, etc, through a parameter page
- Features that cannot be self-described in a parameter page (like number of CE#) shall be host discoverable

ONFI should leverage existing Flash behavior to the extent possible

- Intent is to enable orderly and TTM transition, so highly divergent behavior from existing NAND undesired
- Where prudent for longevity or capability need, existing Flash behavior shall be modified or expanded

ONFI needs to enable future innovation

Initiative Status

Intel is working with key partners to form the ONFI Workgroup

–More details to come shortly

ONFI specification expected to be released in 2H'06

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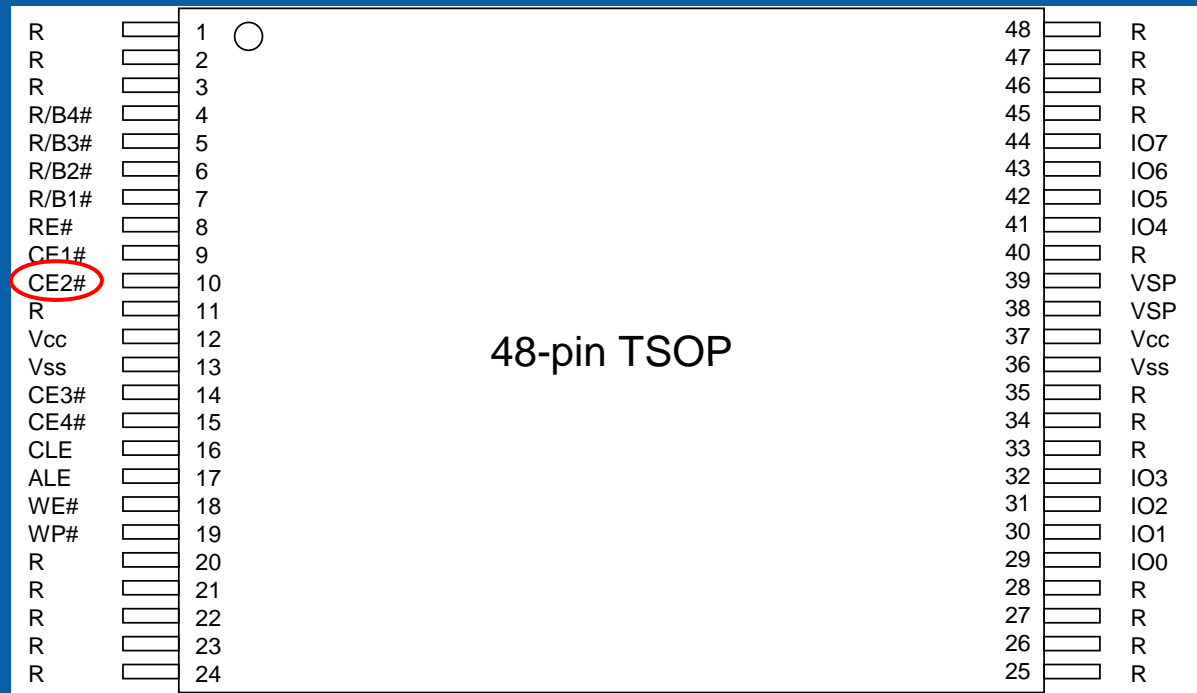
Pin-Out and Package

ONFI defines standard pin-outs for the 48-pin TSOP and 52-pin LGA packages

Pin-out critical for ensuring no board changes required in NAND Flash upgrade

- For example, the host can plan for a new part that will have an additional CE# beforehand

Host can plan for part with additional CE#

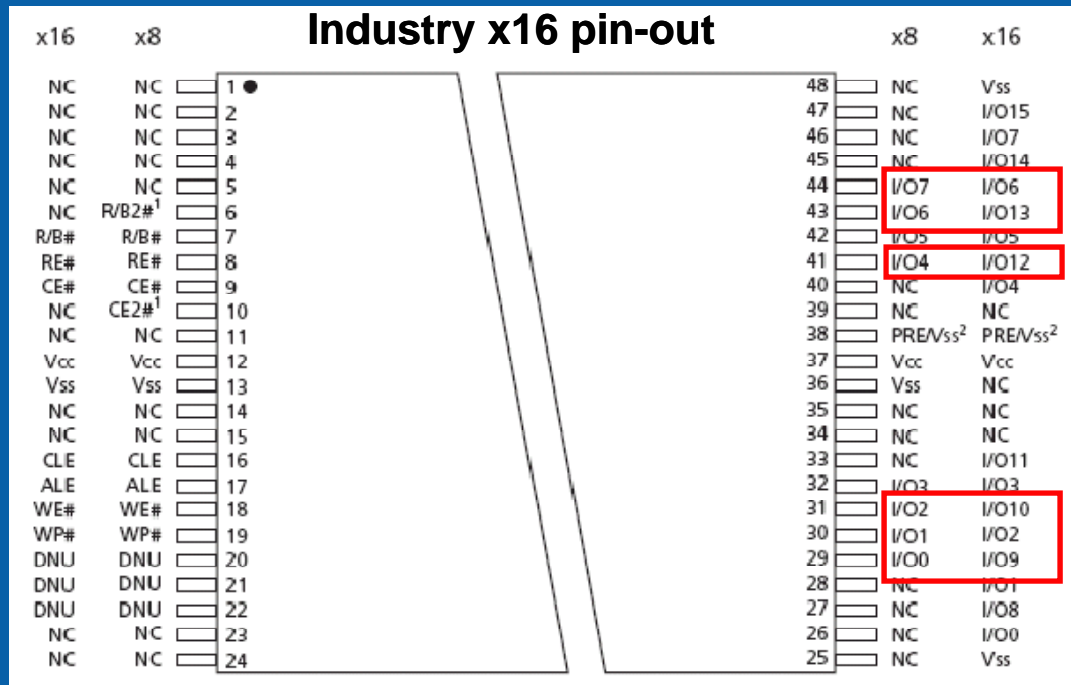


Fixing 16-bit Data Pin-out

The current industry x16 pin-out precludes board designs accepting both x8 and x16 parts easily

- The I/O0 – I/O7 pins are not in the same place!

ONFI is fixing this issue before x16 parts become entrenched (x16 currently is ~ < 1% of volume)



6 of 8 data pins are in different locations on the x16 pin-out!

Device Abstraction

ONFI presents a device representation to the host based on independence “levels”

- ONFI has no notion of number of die or number of planes, etc.

Target: Completely independent unit with its own chip enable (CE_x#)

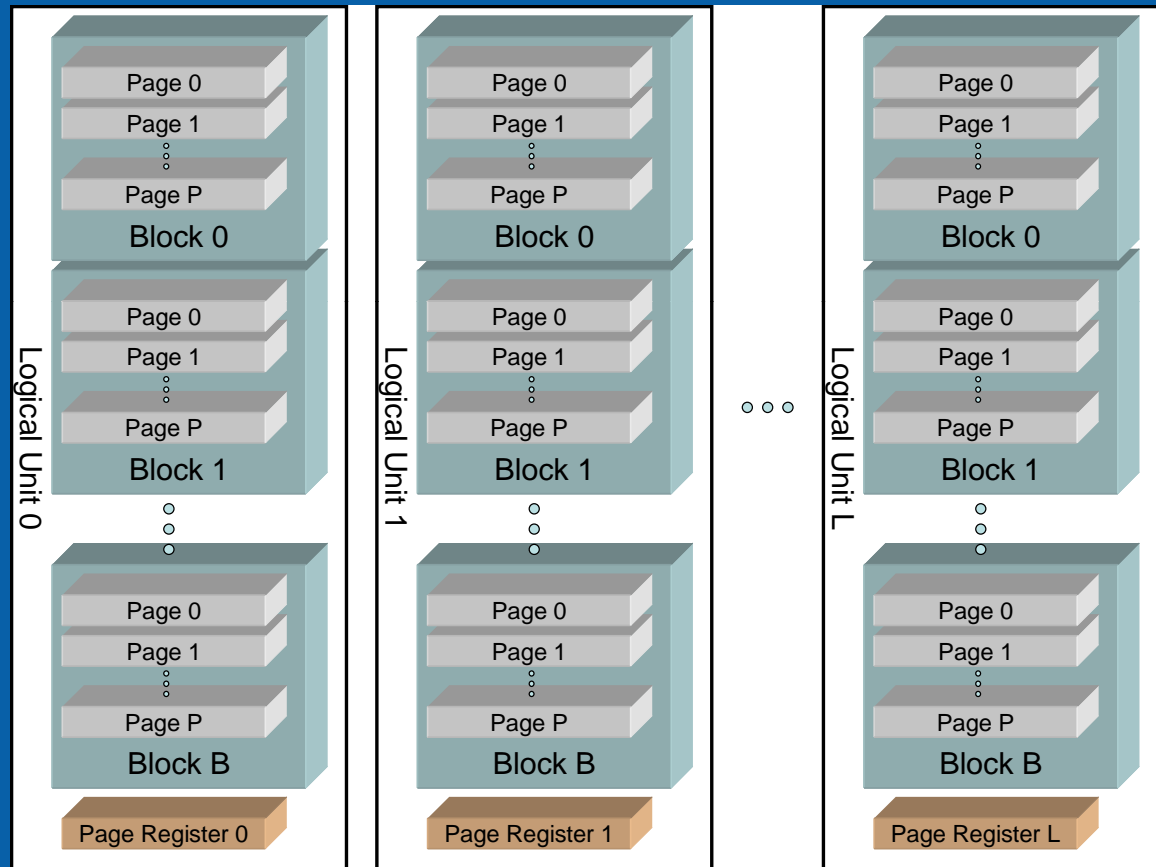
- Logical Unit (LUN): Logically independent unit, shared chip enable
 - Interleaved Addressing: Dependent operations allowed for different blocks with same page address

Targets and LUNs

Each target may support multiple logical units

Each LUN may support interleaved addressing for increased parallelism

Actual implementation abstracted



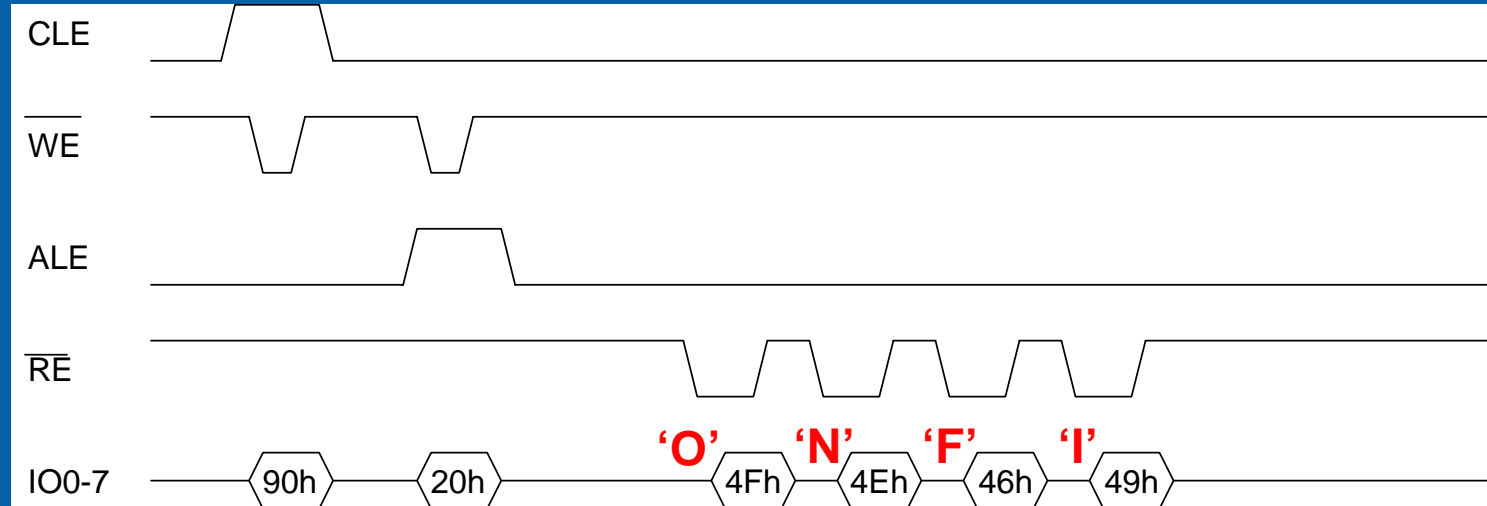
Target X, using CEx#

Determining ONFI Support

Read ID is used by Flash parts today to report device ID for use in chip ID table lookup

ONFI support is shown by responding to Read ID for address 20h with ASCII 'ONFI'

Support for vendor specific interface and ONFI allowed by changing address cycle to 20h from 0h



Self Reporting Capabilities

Each target describes its features and capabilities through a parameter page

Blocks of the parameter page are devoted to:

- Revision information
- Device features
- Manufacturer information
- **Memory organization**
- Timing parameters
- Vendor specific

Memory Organization Block of Parameter Page

Number of data bytes per page

Number of redundant bytes per page

Number of pages per block

Number of blocks per logical unit (LUN)

Number of logical units

Number of address cycles

Number of bits per cell

Block endurance

Number of programs per page

Recommended bits of ECC correction

Interleaved addressing

Command Set Overview

Command	O/M	1 st Cycle	2 nd Cycle	Acceptable while Accessed LUN is Busy	Acceptable while Other LUNs are Busy
Read	M	00h	30h		Y
Change Read Column	M	05h	E0h		Y
Change Read Column Enhanced	O	06h	E0h		Y
Read Cache	O	31h			
Read Cache End	O	3Fh			
Block Erase	M	60h	D0h		Y
Reserved		61h – 6Fh			
Read Status	M	70h		Y	Y
Read LUN Status	O	78h		Y	Y
Page Program	M	80h	10h		Y
Page Cache Program	O	80h	15h		Y
Change Write Column	M	85h			Y
Read ID	M	90h			
Vendor Unique		91h - BFh			
Read Parameter Page	M	ECh			
Get Features	O	EEh			
Set Features	O	EFh			
Reset	M	FFh		Y	Y

Timing Requirements

NAND contains a lot of timing requirements and hence timings

Reporting each and every timing value leads to validation challenge

- Requires validation of all combinations

To make timing information useful, organized into timing modes

Parameter	Description
tADL	Minimum ALE to data loading time
tALH	Minimum ALE hold time
tALS	Minimum ALE setup time
tAR	Minimum ALE to RE# delay
tBERS	Maximum block erase time
tCEA	Maximum CE# access time
tCH	Minimum CE# hold time
tCHZ	Maximum CE# high to output hi-Z
tCLH	Minimum CLE hold time
tCLR	Minimum CLE to RE# delay
...	...
tREH	Minimum RE# high hold time
tRHOH	Minimum RE# high to output hold
tRHW	Minimum RE# high to WE# low
tRHZ	Maximum RE# high to output hi-Z
tRLOH	Minimum RE# low to output hold
tRP	Minimum RE# pulse width
tRR	Minimum Ready to RE# low
tRST	Maximum device reset time
tWB	Maximum WE# high to R/B# low
tWC	Minimum write cycle time
tWH	Minimum WE# high hold time
tWHR	Minimum WE# high to RE# low
tWP	Minimum WE# pulse width

Timing Modes

Timing modes define vast majority of required host timings as one "set"

Three parameters are specified separately in RPP

- Max page read time
- Max block erase time
- Max page program time

Timing modes supported reported in timing parameters block of RPP

Parameter	Mode Example		Unit
	Min	Max	
	30		ns
tADL	100		ns
tALH	5		ns
tALS	10		ns
tAR	10		ns
tCEA		25	ns
tCH	5		ns
tCHZ		20	ns
tCLH	5		ns
tCLR	10		ns
tCLS	15		ns
...	ns
tWB		100	ns
tWC	30		ns
tWH	10		ns
tWHR	60		ns
tWP	15		ns

Interleaved Operation

Interleaving may be used to complete the same operation on additional blocks on a per logical unit basis to enhance performance

- Concurrent interleaving: Operations to all of the blocks is issued at the same time and then executes in parallel
- Overlapped interleaving: Operations may be issued independently, allows host to determine later to do an additional operation

The operations that may be interleaved are reads, programs, and erases

When using interleaving, the lowest order bits of the block address may be modified. The rest of the address must be the same as the other operations being issued on that LUN.



Defect Mapping & Enumeration

An invalid block is indicated by a 00h value in the first or last page of a block

- Ensures robustness in marking bad pages in face of recoverable bit errors

The host uses this information to create its initial bad block table

```
// For each LUN maps defects
for (i = 0; i < NumLUNs; i++) {

    // For each block within this LUN, map defects
    for (j = 0; j < BlocksPerLUN; j++) {
        Defective=FALSE;

        // If a 00h value is in the first page, this block is defective
        ReadPage(lun=i; block=j; page=0; DestBuff=Buff);
        for (column=0; column<PageSize+RedundantBytes; column++) {
            if (Buff[column] == 00h)
                Defective=TRUE;
        }

        // If a 00h value is in the last page, this block is defective
        ReadPage(lun=i; block=j; page=PagesPerBlock-1; DestBuff=Buff);
        for (column = 0; column < PageSize+RedundantBytes; column++) {
            if (Buff[column] == 00h)
                Defective=TRUE;
        }

        // If the block was defective, then keep track of this
        if (Defective)
            MarkBlockDefective(lun=i; block=j);
    }
}
```

ONFI Technical Highlights

ONFI support is identified via Read ID, the standard NAND chip ID command

NAND devices report their capabilities using the Read Parameter Page

ONFI standardizes the base subset of commands required to be supported by all NAND devices

ONFI supports increased performance through parallelism made possible by multiple LUNs and interleaved addressing

ONFI standardizes the pin-out and packaging to ensure no PCB changes are required for a new NAND part

**ONFI provides the solid technical base
necessary to confidently build
NAND-based products**

Summary

Differing implementations of the NAND Flash interface across vendors impacts time to market and revenue

Lack of standard makes it impossible for platforms to support a range of NAND components, including components introduced at a later date

ONFI is being developed to solve the barriers to the rapid adoption of new NAND products

ONFI enables NAND feature self-identification, and standardizes command set, pin-out, and packaging

Please fill out the Session Evaluation Form.

Additional sources of information on this topic:

IDF Chalk Talk, MEMC007: Upcoming Flash and Main Memory
Technologies and Applications

Initiative updates available at: www.onfi.org

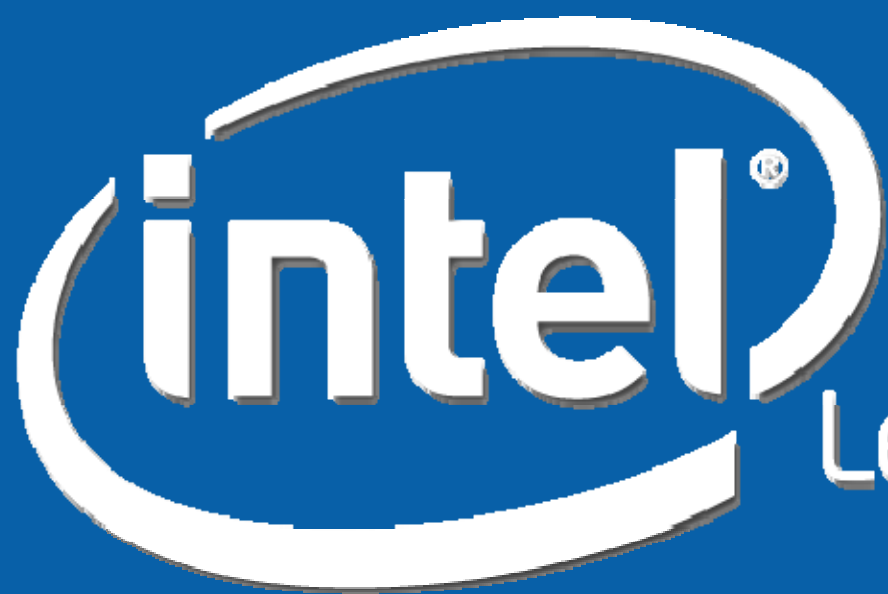
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